

# **SEMICONDUCTOR STRUCTURE AND METHOD FOR FABRICATING SAME**

## **ABSTRACT**

Embodiments provide a semiconductor structure and a method for fabricating same. The semiconductor structure includes: a source region and a drain region arranged at intervals on a substrate; a gate oxide layer arranged between the source region and the drain region; a gate structure arranged on the gate oxide layer; and a conductive plug arranged at a corresponding position of the source region and a corresponding position of the drain region. The gate structure includes a conductive layer having an inclined side surface facing toward the conductive plug. Compared with a traditional gate structure, in the solutions of the present application, a distance between the conductive layer having the inclined side surface and the conductive plug is increased, thereby reducing a parasitic capacitance between the gate structure and the conductive plug, such that capacitance between a gate and the source/drain region is reduced, and device characteristics are improved.

[Fig. 2a]